Vincotech

10-PZ12B2A075ME-P621L18Y
datasheet

flowBOOST 0 dual SiC **1200 V / 75 mΩ**

Topology features

- Kelvin Emitter for improved switching performance
- Dual Booster
- Bypass Diode
- Open Emitter configuration
- Temperature sensor

Component features

- High Blocking Voltage with low drain source on state resistance
- High speed SiC-MOSFET technology
- Resistant to Latch-up

Housing features

- Base isolation: Al_2O_3
- Clip-in, reliable mechanical connection, qualified for wave soldering
- Convex shaped substrate for superior thermal contact
- Thermo-mechanical push-and-pull force relief
- Press-fit pin
- Reliable cold welding connection

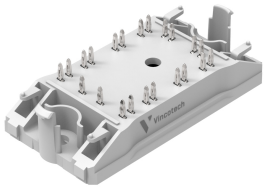
Target applications

- Solar Inverters

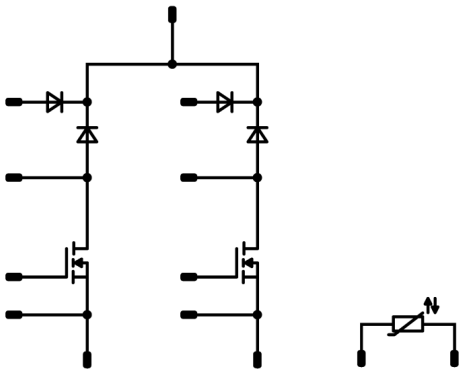
Types

- 10-PZ12B2A075ME-P621L18Y

flow 0 12 mm housing



Schematic



Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Boost Switch				
Drain-source voltage	V_{DSS}		1200	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$ T_s = 80 °C	20	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	80	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	52	W
Gate-source voltage	V_{GSS}		-4 / 15	V
		dynamic	-8 / 19	
Maximum Junction Temperature	T_{jmax}		175	°C
Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	19	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	52	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms T_j = 25 °C	92	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	58	W
Maximum junction temperature	T_{jmax}		175	°C
ByPass Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	38	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms T_j = 150 °C	270	A
Surge current capability	I^2t		370	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	47	W
Maximum junction temperature	T_{jmax}		150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage t_p = 1 min	2500	V
Creepage distance			min 12,7	mm
Clearance			9,15	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		15		20	25 125 150		76,2 105 116	90(1)	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,005	25	1,7	2,5	4	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		10	250	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	1200		25		1	100	µA
Internal gate resistance	r_g							10,5		Ω
Gate charge	Q_g		-4/15	800	20	25		54		nC
Short-circuit input capacitance	C_{iss}	f = 1 Mhz	0	1000	0	25		1350		pF
Short-circuit output capacitance	C_{oss}							58		
Reverse transfer capacitance	C_{rss}							3		
Diode forward voltage	V_{SD}		0		10	25		4,5		V
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,84		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 8 Ω R_{goff} = 8 Ω	0/15	700	16	25 125 150		14,4 12,8 12,48		ns
Rise time	t_r					25 125 150		9,28 9,28 8,96		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		69,76 78,4 80,96		ns
Fall time	t_f					25 125 150		27,91 30,9 32,13		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,119 µC Q_{rFWD}=0,113 µC Q_{rFWD}=0,111 µC				25 125 150		0,235 0,216 0,212		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,08 0,087 0,091		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Diode										
Static										
Forward voltage	V_F				10	25 125 150		1,43 1,73 1,84	1,8[1]	V
Reverse leakage current	I_R	V_r = 1200 V				25		40	300	µA
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,64		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt=2071 A/µs di/dt=2263 A/µs di/dt=2290 A/µs	0/15	700	16	25 125 150		7,75 8,71 8,88		A
Reverse recovery time	t_{rr}					25 125 150		26,16 24,28 23,87		ns
Recovered charge	Q_r					25 125 150		0,119 0,113 0,111		µC
Reverse recovered energy	E_{rec}					25 125 150		0,047 0,044 0,043		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		733,99 1159 1267		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
ByPass Diode										
Static										
Forward voltage	V_F				28	25 125		1,15 1,1	1,5[1]	V
Reverse leakage current	I_R	V_r = 1600 V				25 150			100 1000	µA
Thermal										
Thermal resistance junction to sink [2]	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,5		K/W
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		130		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

[1] Value at chip level

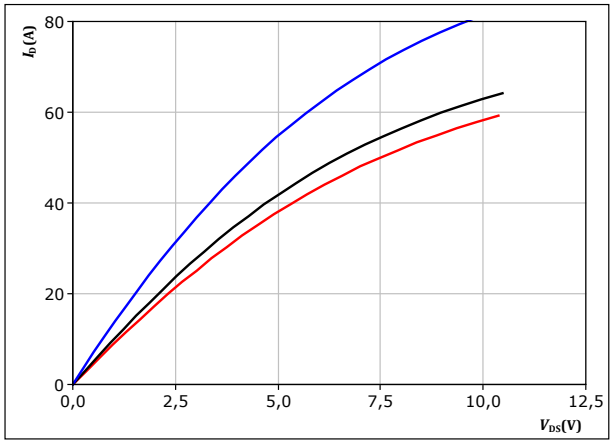
[2] Only valid with pre-applied Vincotech thermal interface material.

Boost Switch Characteristics

figure 1. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$

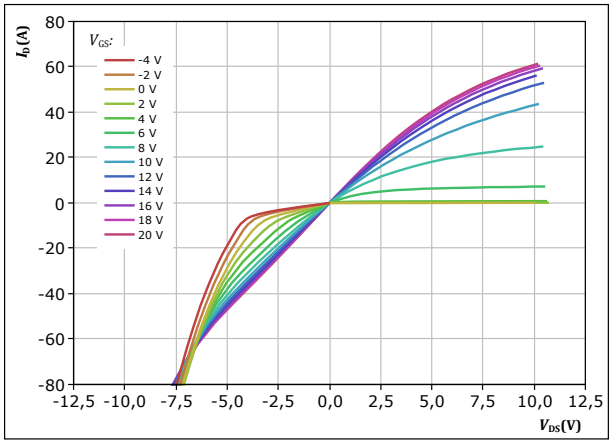


t_p =	250	µs		
V_{GS} =	16	V	T_j:	25 °C
				125 °C
				150 °C

figure 2. **MOSFET**

Typical output characteristics

$I_D = f(V_{DS})$



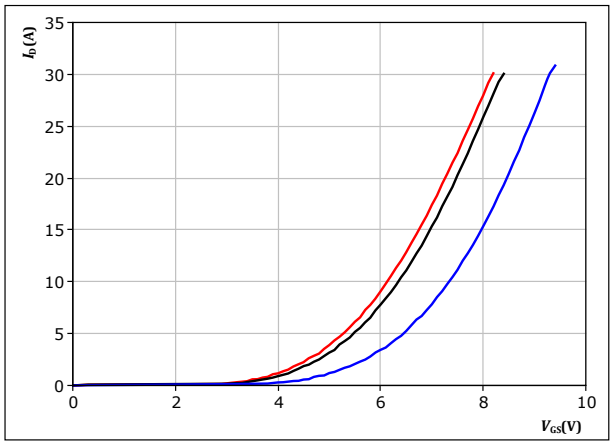
t_p =	250	µs
T_j =	150	°C

V_{GS} from -4 V to 20 V in steps of 2 V

figure 3. **MOSFET**

Typical transfer characteristics

$I_D = f(V_{GS})$

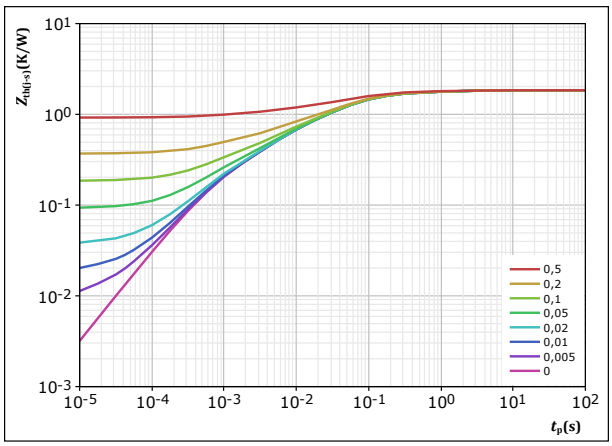


t_p =	250	µs		
V_{DS} =	10	V	T_j:	25 °C
				125 °C
				150 °C

figure 4. **MOSFET**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	1,843	K/W

MOSFET thermal model values

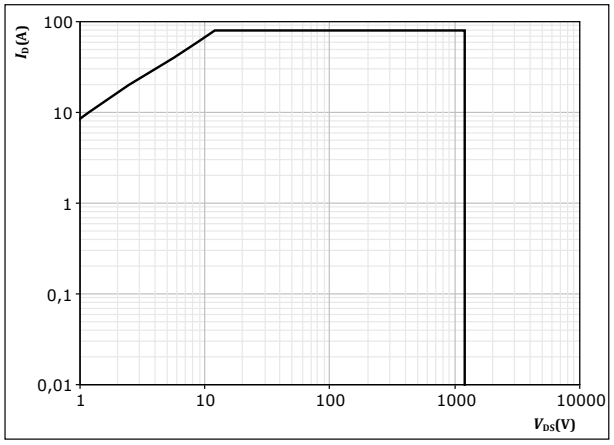
R (K/W)	τ (s)
1,10E-01	1,89E+00
4,15E-01	1,55E-01
7,53E-01	3,96E-02
4,02E-01	6,20E-03
1,64E-01	7,03E-04

Boost Switch Characteristics

figure 5. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$



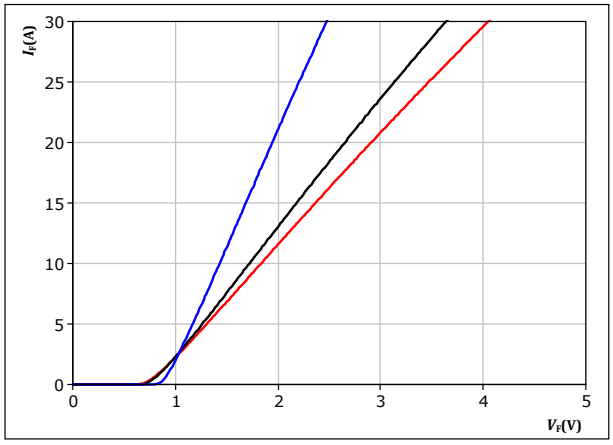
D =	single pulse	
T_s =	80	°C
V_{GS} =	16	V
T_j =	T_{jmax}	

Boost Diode Characteristics

figure 6. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



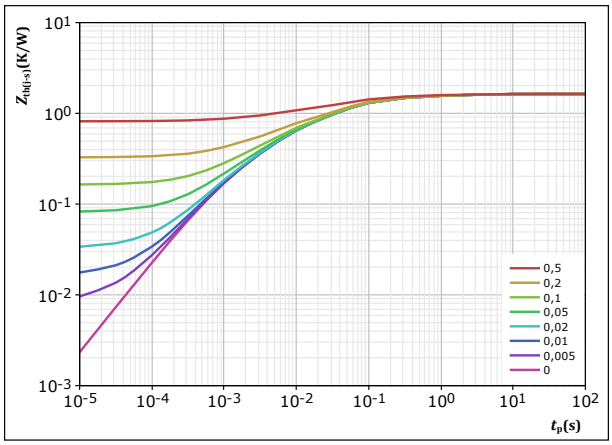
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 7. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,635 K/W

FWD thermal model values

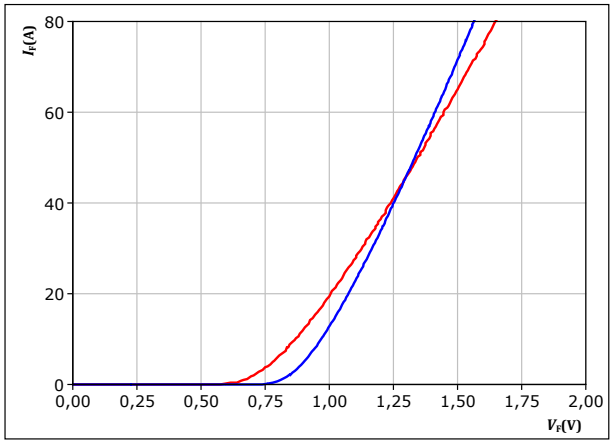
R (K/W)	τ (s)
1,05E-01	2,56E+00
2,66E-01	2,22E-01
7,28E-01	4,00E-02
4,30E-01	5,14E-03
1,07E-01	8,14E-04

ByPass Diode Characteristics

figure 8. **Rectifier**

Typical forward characteristics

$I_F = f(V_F)$



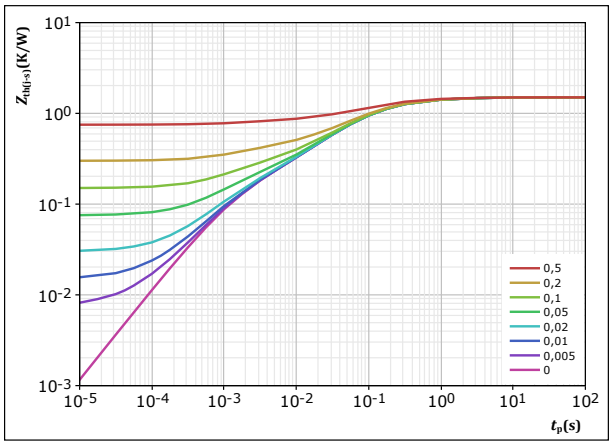
t_p = 250 µs

T_j: 25 °C, 125 °C

figure 9. **Rectifier**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,5 K/W

Rectifier thermal model values

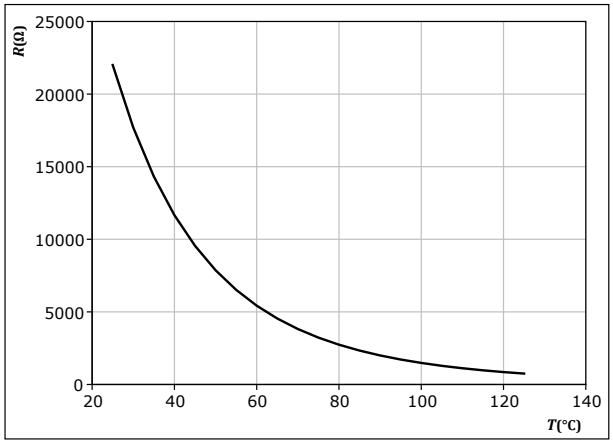
R (K/W)	τ (s)
9,44E-02	2,48E+00
3,47E-01	3,51E-01
7,44E-01	7,63E-02
2,04E-01	1,21E-02
1,11E-01	1,25E-03

Thermistor Characteristics

figure 10. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

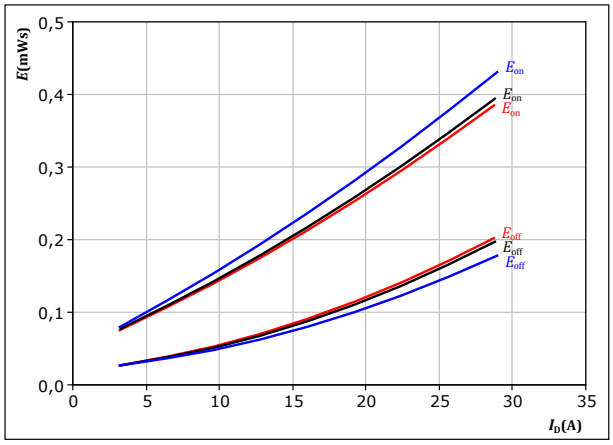


Boost Switching Characteristics

figure 11. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



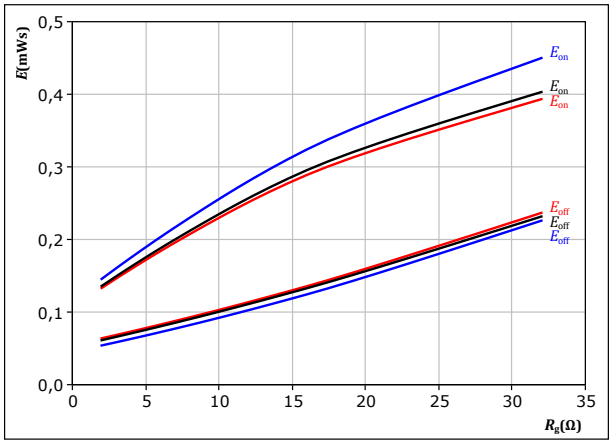
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	0/15	V		125 °C
R_{gon} =	8	Ω		150 °C
R_{goff} =	8	Ω		

figure 12. **MOSFET**

Typical switching energy losses as a function of MOSFET turn on gate resistor

$E = f(R_g)$



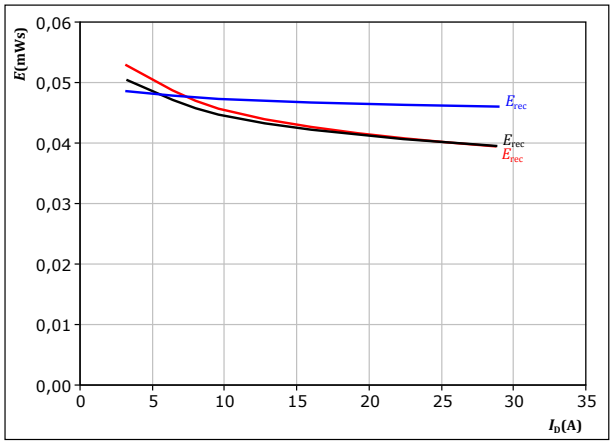
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	0/15	V		125 °C
I_D =	16	A		150 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



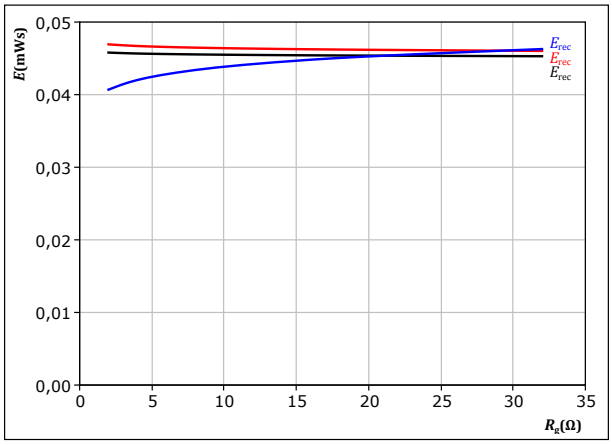
With an inductive load at

V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	0/15	V		125 °C
R_{gon} =	8	Ω		150 °C

figure 14. **FWD**

Typical reverse recovered energy loss as a function of MOSFET turn on gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

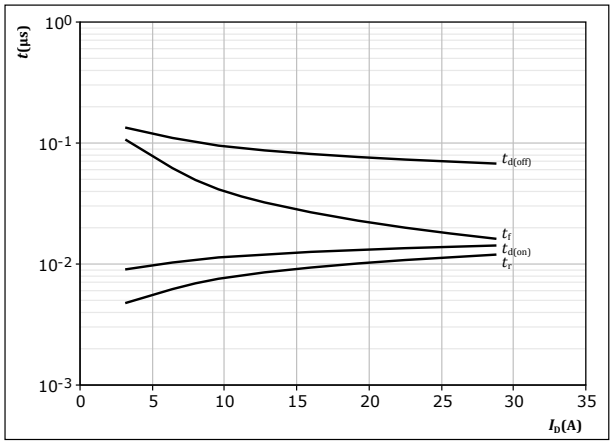
V_{DS} =	700	V	T_j:	25 °C
V_{GS} =	0/15	V		125 °C
I_D =	16	A		150 °C

Boost Switching Characteristics

figure 15. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



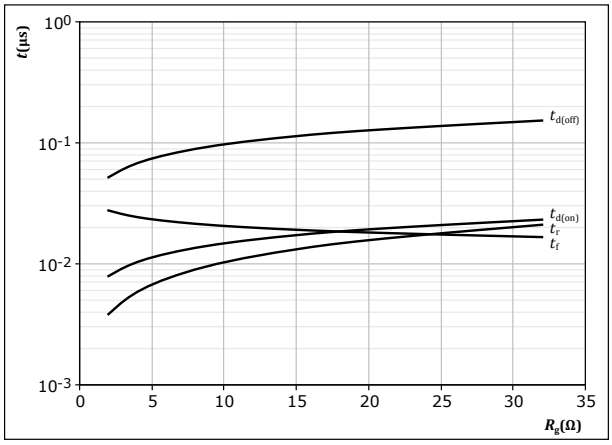
With an inductive load at

T_j =	150	°C
V_{DS} =	700	V
V_{GS} =	0/15	V
R_{gon} =	8	Ω
R_{goff} =	8	Ω

figure 16. **MOSFET**

Typical switching times as a function of MOSFET turn on gate resistor

$t = f(R_g)$



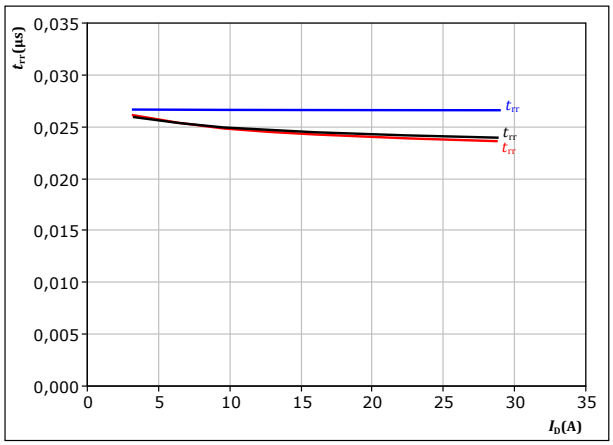
With an inductive load at

T_j =	150	°C
V_{DS} =	700	V
V_{GS} =	0/15	V
I_D =	16	A

figure 17. **FWD**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



At

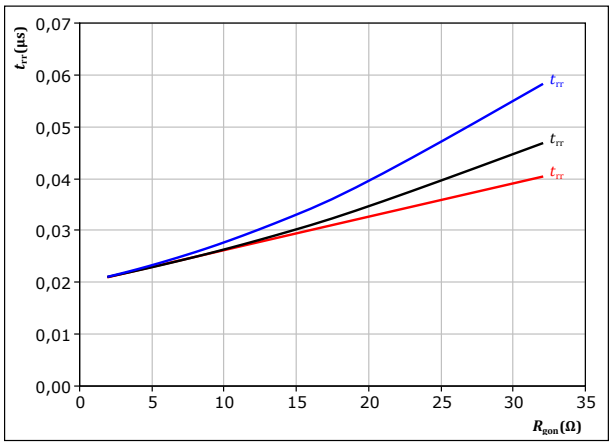
V_{DS} =	700	V
V_{GS} =	0/15	V
R_{gon} =	8	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 18. **FWD**

Typical reverse recovery time as a function of MOSFET turn on gate resistor

$t_{rr} = f(R_{gon})$



At

V_{DS} =	700	V
V_{GS} =	0/15	V
I_D =	16	A

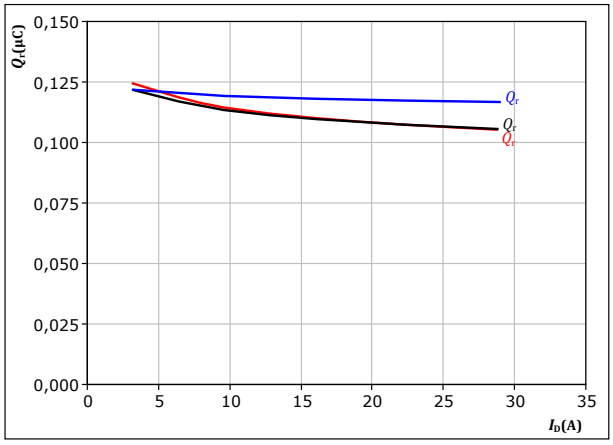
T_j: 25 °C, 125 °C, 150 °C

Boost Switching Characteristics

figure 19. **FWD**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

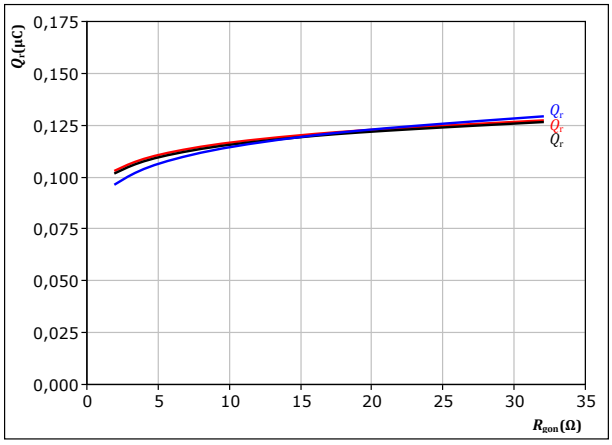


At					
	V_{DS} =	700	V		
	V_{GS} =	0/15	V	T_j:	25 °C
	R_{gon} =	8	Ω		125 °C
					150 °C

figure 20. **FWD**

Typical recovered charge as a function of MOSFET turn on gate resistor

$Q_r = f(R_{gon})$

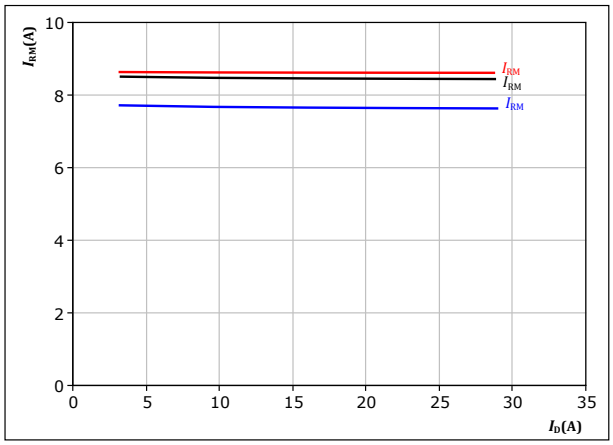


At					
	V_{DS} =	700	V		
	V_{GS} =	0/15	V	T_j:	25 °C
	I_D =	16	A		125 °C
					150 °C

figure 21. **FWD**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

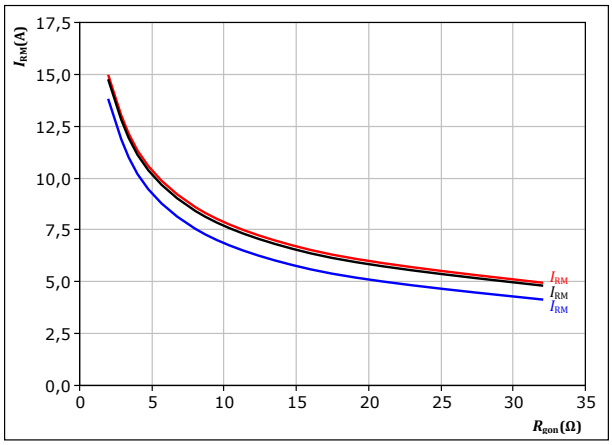


At					
	V_{DS} =	700	V		
	V_{GS} =	0/15	V	T_j:	25 °C
	R_{gon} =	8	Ω		125 °C
					150 °C

figure 22. **FWD**

Typical peak reverse recovery current as a function of MOSFET turn on gate resistor

$I_{RM} = f(R_{gon})$



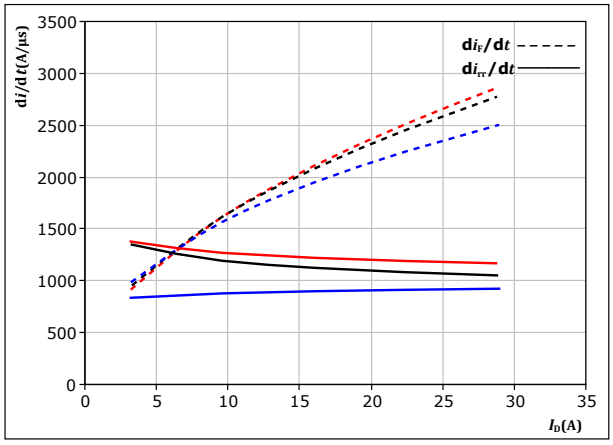
At					
	V_{DS} =	700	V		
	V_{GS} =	0/15	V	T_j:	25 °C
	I_D =	16	A		125 °C
					150 °C

Boost Switching Characteristics

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

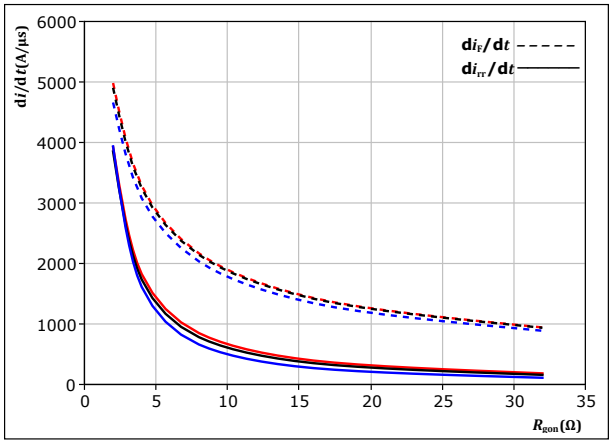


At				
	V_{DS} =	700	V	
	V_{GS} =	0/15	V	T_j: 25 °C, 125 °C, 150 °C
	R_{gon} =	8	Ω	

figure 24. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor

di_F/dt, di_{rr}/dt = f(R_{gon})

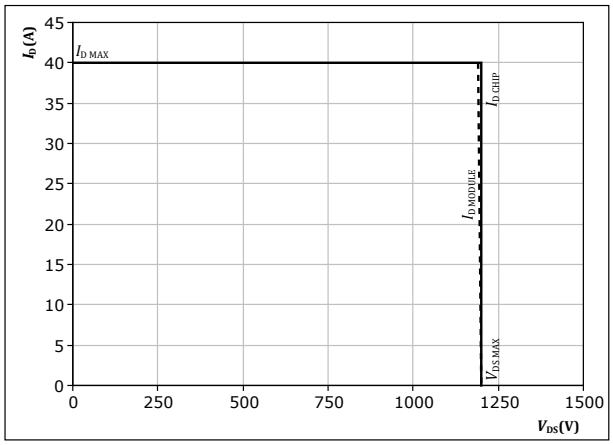


At				
	V_{DS} =	700	V	
	V_{GS} =	0/15	V	T_j: 25 °C, 125 °C, 150 °C
	I_D =	16	A	

figure 25. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At			
	T_j =	150	°C
	R_{gon} =	8	Ω
	R_{goff} =	8	Ω

Boost Switching Definitions

figure 26. MOSFET

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

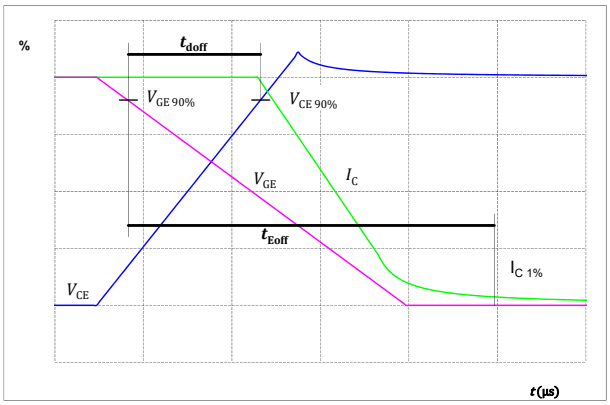


figure 27. MOSFET

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

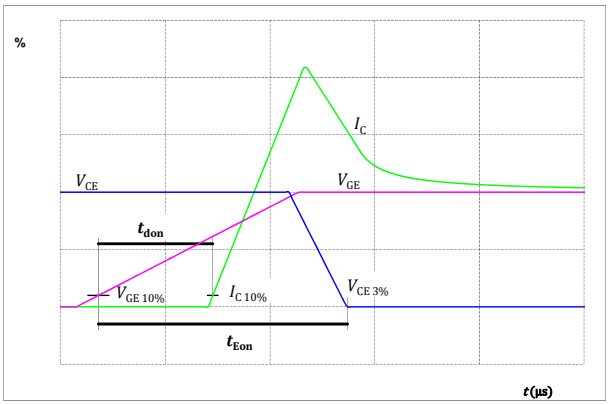


figure 28. MOSFET

Turn-off Switching Waveforms & definition of t_f

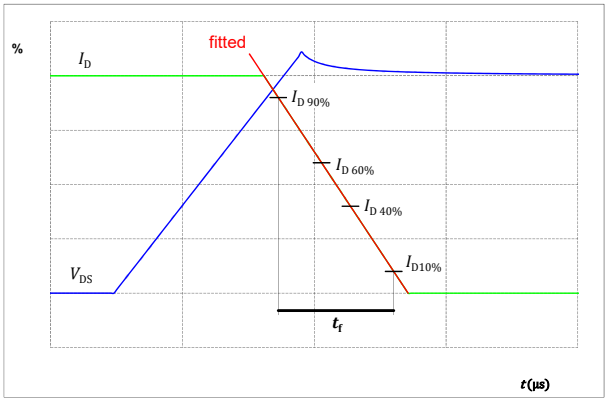
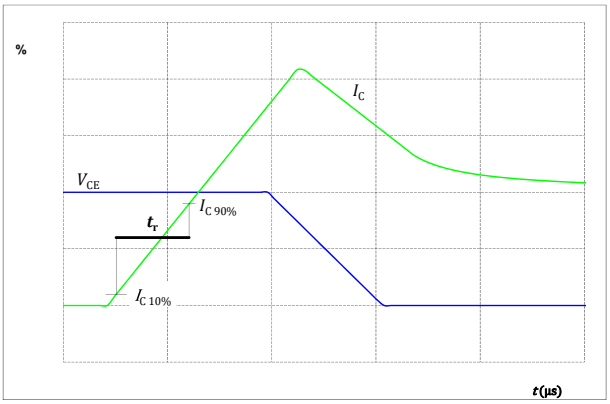


figure 29. MOSFET

Turn-on Switching Waveforms & definition of t_r



Boost Switching Definitions

figure 30. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

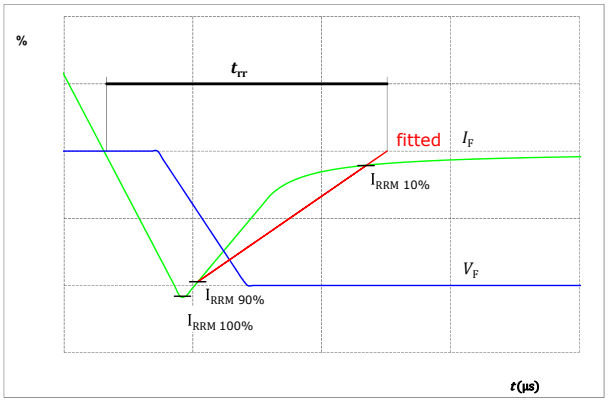


figure 31. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

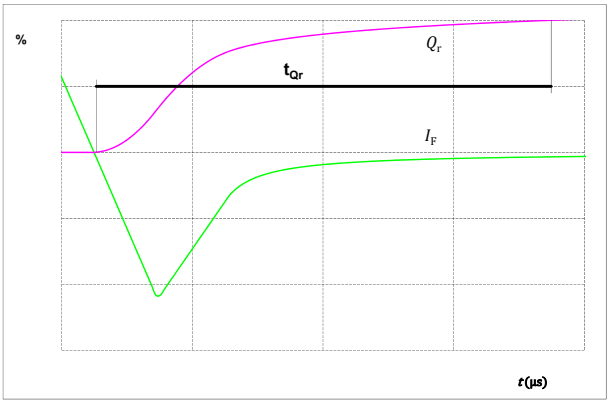
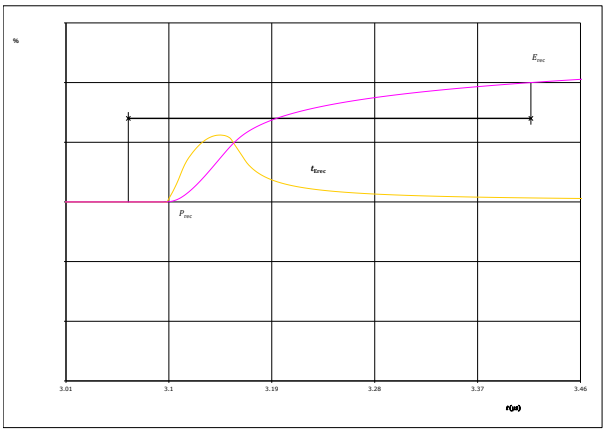


figure 32. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Ordering Code

Version	Ordering Code
Without thermal paste	10-PZ12B2A075ME-P621L18Y
With thermal paste (5,2 W/mK, PTM6000HV)	10-PZ12B2A075ME-P621L18Y-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-PZ12B2A075ME-P621L18Y-/3/

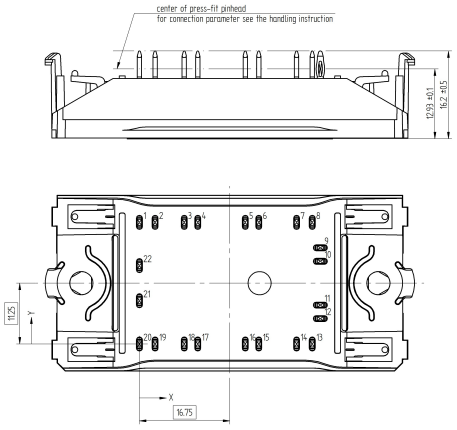
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

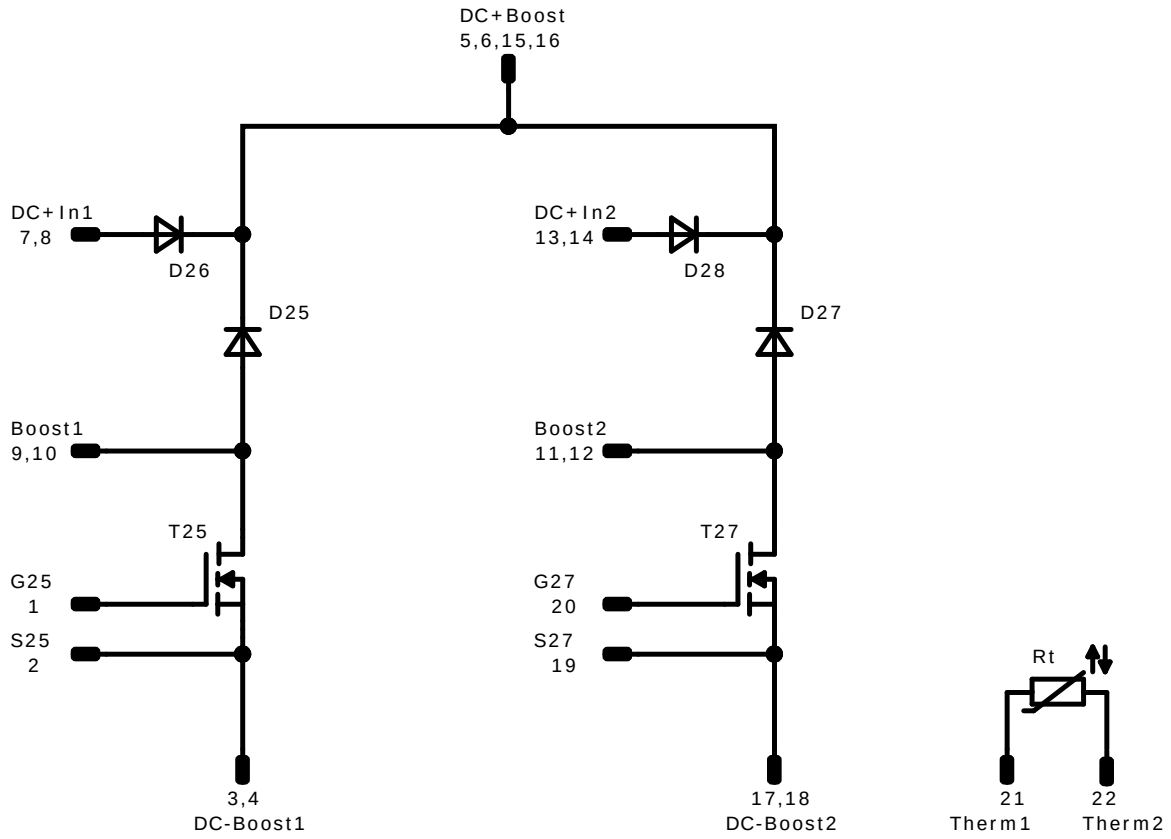
Pin table [mm]

Pin	X	Y	Function
1	0	22,5	G25
2	2,9	22,5	S25
3	8,3	22,5	DC-Boost1
4	10,8	22,5	DC-Boost1
5	19,6	22,5	DC+Boost
6	22,1	22,5	DC+Boost
7	29,1	22,5	DC+In1
8	32	22,5	DC+In1
9	33,5	17,8	Boost1
10	33,5	15,3	Boost1
11	33,5	7,2	Boost2
12	33,5	4,7	Boost2
13	32	0	DC+In2
14	29,1	0	DC+In2
15	22,1	0	DC+Boost
16	19,6	0	DC+Boost
17	10,8	0	DC-Boost2
18	8,3	0	DC-Boost2
19	2,9	0	S27
20	0	0	G27
21	0	8	Therm1
22	0	14,5	Therm2



Tolerance of pinpositions ±0.5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T25, T27	MOSFET	1200 V	75 mΩ	Boost Switch	
D25, D27	FWD	1200 V	10 A	Boost Diode	
D26, D28	Rectifier	1600 V	28 A	ByPass Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-PZ12B2A075ME-P621L18Y-D2-14	5 May. 2022	-/7/ ordering option added New Datasheet format, module is unchanged	